

Vishay Siliconix

Power Down Fault Protected, 1.8 V to 5.5 V, 2.5 Ω , 4-Channel (4:1) Multiplexer

DESCRIPTION

The DG2034E is a four-channel multiplexer that operates with a single 1.8 V to 5.5 V power supply. It features power down fault protection that prevents excessive current flow when V+ is to ground.

The device's low power dissipation and wide voltage range make it ideal for use in battery powered products. The ultra low capacitance and charge injection of the switch make it an ideal solution for data acquisition and sample and hold applications, where low glitch and fast settling are required. Low switch resistance and fast switching speeds, together with high signal bandwidth, make the DG2034E suitable for video signal switching.

The DG2034E switches one of four inputs to a common output as determined by the 3-bit binary address lines: A0, A1, and EN. Each switch conducts equally well in both directions when on, blocks input voltages up to the supply level when off, and exhibits break before make switching action.

The device's high ESD and latch-up current capability make it more reliable in designs where the part sits close to the interface.

The DG2034E is available in MSOP10 and QFN12 3 mm x 3 mm packages.

FEATURES

- 2.5 Ω switch on-resistance
- 7 pF source-off capacitance
- 27 pF comm-off capacitance
- 33 pF comm-on capacitance
- 13 ns turn-on time
- -2 pC charge injection
- -67 dB off-isolation at 1 MHz
- -71 dB crosstalk at 1 MHz
- 166 MHz bandwidth
- 8 kV ESD / HBM
- 400 mA latch-up current

BENEFITS

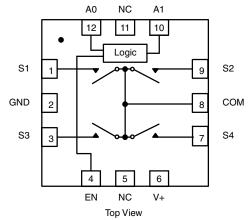
- Power down fault protection
- · Low parasitic and charge injection
- Wide operation voltage range
- High ESD tolerance

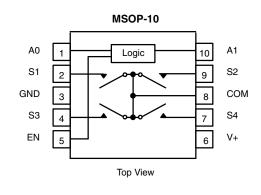
APPLICATIONS

- · Automatic test equipment
- Process control and automation
- Data acquisition systems
- · Meters and instruments
- Medical and healthcare systems
- Communication systems
- · Audio and video switching
- · Relay replacements

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

12-Pin QFN (3 mm x 3 mm)





Document Number: 73172



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TRUTH TABLE							
A1	A0	EN	ON SWITCH				
Х	Х	0	None				
0	0	1	S1				
0	1	1	S2				
1	0	1	S3				
1	1	1	S4				

ORDERING INFORMATION						
TEMP. RANGE	PACKAGE	PART NUMBER				
-40 °C to +85 °C	MSOP-10	DG2034EDQ-T1-GE3				
	12-pin QFN (3 mm x 3 mm)	DG2034EDN-T1-GE4				

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		LIMIT	UNIT			
Referenced V+ to GND		-0.3 to +6	V			
A _X , EN, S _X , COM ^a		-0.3 to (V+ + 0.3)]			
Continuous current (any terminal)		± 50	A			
Peak current (pulsed at 1 ms, 10 % duty c	± 100	- mA				
Device discipation (package)	QFN-12 (3 mm x 3 mm) ^c	1295	\A/			
Power dissipation (package) ^b	MSOP-10 d	320	- mW			
Storage temperature (D suffix)		-65 to +150	°C			
ESD / HBM	EIA / JESD22-A114-A	8k	V			
ESD / CDM	EIA / JESD22-C101-A	2k	- V			
Latch up	JESD78	400	mA			

Notes

- $a. \quad Signals \ on \ S_X, COM, EN \ or \ A_X \ exceeding \ V+ \ or \ V- \ will \ be \ clamped \ by \ internal \ diodes. \ Limit \ forward \ diode \ current \ to \ maximum \ current \ ratings$
- b. All leads welded or soldered to PC board
- c. Derate 16.2 mV/°C above 70 °C
- d. Derate 4 mV/°C above 70 °C



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SPECIFICATIONS (V+ =	3 V)							
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED		TEMP.a	LIMITS -40 to +85 °C		°C	UNIT
	$V+ = 3 V, \pm 10 \%, V_{AL} = 0.5 V, V_{AH} = 1.5 V^{e}$		_H = 1.5 V ^e		MIN. c	TYP. b	MAX. c	
Analog Switch								
Analog signal range d	V _{ANALOG}			Full	0	-	V+	V
		V: 18VV 04V/V: I	Ο να Λ	Room	-	7	10	
Drain-source	В	$V+ = 1.8 \text{ V}, V_S = 0.4 \text{ V} / V+, I_S = 0.4 \text{ V}$	= 0 IIIA	Full	-	-	11	
On-resistance	R _{DS(on)}	V. 07VV 00V/10VI	10 1	Room	-	4.6	5.3	
		$V+ = 2.7 \text{ V}, V_{COM} = 0.8 \text{ V} / 1.8 \text{ V} I_{CC}$	M = 10 MA	Full	-	-	5.9	
On registance metabling	AD			Room	-	0.02	0.27	Ω
On-resistance matching	$\Delta R_{DS(on)}$	$V+ = 2.7 \text{ V}, V_{COM} = 0.8 \text{ V} / 1.4 \text{ V}$	/ / 1.8 V	Full	-	-	0.41	
O a satisfie and flat and diff	Б	I _{COM} = 10 mA		Room	-	0.62	1	
On-resistance flatness d, f	R _{flat(on)}			Full	-	-	1.3	
Office Land and the Control of the Co				Room	-2	0.01	2	
Off leakage current ^g	I _{S(off)}	$V+ = 3.3 \text{ V}, V_S = 1 \text{ V} / 3 \text{ V}$	/	Full	-5	-	5	
		$V_{COM} = 3 \text{ V} / 1 \text{ V}, V_{EN} = 0$	V	Room	-2	0.01	2	
COM off leakage current ^g	ICOM(off)			Full	-5	-	5	nA
		V+ = 3.3 V		Room	-2	0.01	2	
Channel-on leakage current ^g	I _{COM(on)}	$V_{COM} = V_S = 1 \text{ V} / 3 \text{ V}$		Full	-5	-	5	
Digital Control								
Input current ^d	I _A or I _{EN}	$V_{A/EN} = 0 \text{ V or V+, see truth table}$		Full	-1	0.05	1	μA
Input high voltage ^d	V _{AH} or V _{ENH}			Full	1.5	1.25	-	.,
Input low voltage d	V _{AL} or V _{ENL}			Full	-	1	0.5	V
Digital input capacitance d	C _{IN}			Room	-	3	-	pF
Dynamic Characteristics								
-				Room	-	19	29	
Turn-on time	t _{ON}			Full	-	-	39	
	_	., , ., ., ., ., ., ., ., ., ., ., ., .,		Room	-	16	26	
Turn-off time	t _{OFF}	$V_S = 1.5 \text{ V}, C_L = 35 \text{ pF}, R_L = 3$	300 Ω	Full	-	-	36	
	_			Room	7	12	-	ns
Break-before-make time d	t _{BBM}			Full	5	-	-	
				Room	-	26	41	
Transition time	t _{trans}	$V_S = 1.5 \text{ V} / 0 \text{ V}, V_S = 0 \text{ V} / 1.5 \text{ V}, F$	$R_L = 300 \Omega$	Full	-	-	51	
Charge injection ^d	Q _{INJ}	C _L = 1 nF, V _{qen} = 1.5 V, R _{qen} :	= 0 Ω	Room	-	-2	-	рС
Bandwidth ^d	BW	$C_L = 5 \text{ pF}$ (set up capacitan		Room	-	166	-	MHz
			f = 1 MHz	Room	_	-67	_	+2
Off-isolation ^d	OIRR	$B_i = 50 \Omega C_i = 5 \text{ pF}$	f = 10 MHz	Room	-	-52	-	
		X _{TALK}	f = 1 MHz	Room	-	-71	_	dB
Channel-to-channel crosstalk d	X _{TALK}		f = 10 MHz	Room	-	-55	_	
Off capacitance d	C _{S(off)}	V+ = 2.7 V, f = 1 MHz		Room	-	7	_	
COM off capacitance d	C _{COM(off)}			Room	-	27	_	pF
COM on capacitance d	C _{COM(on)}			Room	_	33	_	۳.
Power Supply	COIVI(on)			1.00111				
Power supply range	V+			Full	2.7	T -	3.3	V
Power supply range	I+	$V_{+} = 2.7 \text{ V}, V_{A/EN} = 0 \text{ V or } 2.7 \text{ V}, \text{ see truth table}$		Full	-	-	1	μA
1 Ower Supply Culterit	IT	$v+=2.1$ v, $v_{A/EN}=0$ v or 2.7 v, see truth table		i uli		<u> </u>	'	μΛ

Notes

- a. Room = 25 °C, Full = as determined by the operating suffix
- b. Typical values are for design aid only, not guaranteed nor subject to production testing
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- d. Guarantee by design, not subjected to production test
- e. V_A, EN = input voltage to perform proper function
- f. Difference of min. and max. values
- g. Guaranteed by 5 V testing

Vishay Siliconix

SPECIFICATIONS (V+ =	J V)				i	LIBAITO		i
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED V+ = 5 V, \pm 10 %, V_{AL} = 0.5 V, V_{AH} = 2 V $^{\circ}$		TEMP.a	LIMITS -40 to +85 °C			UNIT
	• • • • • • • • • • • • • • • • • • • •				MIN. c	TYP. b	MAX. c	
Analog Switch								
Analog signal range ^d	V _{ANALOG}			Full	0	-	V+	V
Drain-source	R _{DS(on)}	$V+ = 4.5 \text{ V}, V_{COM} = 0.8 \text{ V} /$	3.5 V	Room	-	2.5	3.1	
On-resistance	"DS(on)	I _{COM} = 10 mA		Full	-	-	4	
On-resistance matching	$\Delta R_{DS(on)}$			Room	-	0.02	0.29	Ω
On-resistance matering	Δi iDS(on)	$V+ = 4.5 \text{ V}, V_{COM} = 0.8 \text{ V} / 2.5$	V / 3.5 V	Full	-	-	0.42	52
On-resistance flatness d, f	R _{flat(on)}	$I_{COM} = 10 \text{ mA}$		Room	-	0.6	0.9	
On-resistance natness	' 'flat(on)			Full	-	-	1.2	
Off leakage current ^g	laa			Room	-2	0.17	2	
On leakage current 9	I _{S(off)}	$V+ = 5.5 V, V_S = 1 V / 4.5$		Full	-8	-	8	
COM off leakage current ^g	1	$V_{COM} = 4.5 \text{ V} / 1 \text{ V}, V_{EN} =$	0 V	Room	-5	0.77	5	nA
COM on leakage current 9	I _{COM(off)}			Full	-15	-	15	IIA
Channel on lookage ourrent (V+ = 5.5 V, V _{COM} = V _S = 1 V	/ 1 E \/	Room	-5	0.61	5	
Channel-on leakage current ^g	I _{COM(on)}	$V+=5.5 \text{ V}, \text{ V}_{COM}=\text{V}_{S}=1 \text{ V}$	/ 4.5 V	Full	-15	-	15	
Power down leakage d	1	$V+ = 0 V, V_D = 5.5 V, S_X o$	pen	Full	-	0.01	5	μA
Fower down leakage s	I _{PD}	V+ = 0 V, V _S = 5.5 V, COM, open		Full	-	0.01	5	μΑ
Digital Control								
Input current ^d	I _A or I _{EN}	$V_{A/EN} = 0 \text{ V or V+, see truth table}$		Full	-	0.01	1	μΑ
Input high voltage ^d	V _{AH} or V _{ENH}			Full	2	1.76	-	V
Input low voltage ^d	V _{AL} or V _{ENL}			Full	-	1.3	0.5	V
Digital input capacitance d	C _{IN}			Room	-	3	-	pF
Dynamic Characteristics								
Turn-on time	+			Room	-	13	25	
rum-on time	t _{ON}			Full	-	-	35	
Turn-off time	+	$V_S = 3 \text{ V, } C_L = 35 \text{ pF, } R_L = 3 \text{ PF, } R_L $	200 0	Room	-	12	20	
rum-on ume	t _{OFF}	νς = 3 ν, ο _L = 33 μι , η _L = 3	500 52	Full	-	-	30	ns
Break-before-make time d	+			Room	4	10	-	
Break-before-make time -	t _{BBM}			Full	3	-	-	
Transition time	+	V - 3 V / 0 V V - 0 V / 3 V P	- 200 0	Room	-	17	32	
Transition time	t _{trans}	$V_S = 3 V / 0 V, V_S = 0 V / 3 V, R$	L = 300 22	Full	-	-	42	
Propagation delay ^d	t _{PD}	$V+ = 5 V$, no R_{LOAD}		Room	-	537	-	ps
Charge injection ^d	Q_{INJ}	$C_L = 1 \text{ nF}, V_{gen} = 2.5 \text{ V}, R_{gen}$	$_{1} = 0 \Omega$	Room	-	-2.6	-	рC
Bandwidth ^d	BW	C _L = 5 pF (set up capacita	nce)	Room	-	166	-	MHz
Off-isolation d	OIRR	P. = 50 0 C. = 5 pE	f = 1 MHz	Room	-	-67	-	
OII-ISOIATIOII	Oikr	$R_L = 50 \Omega, C_L = 5 pF$ $f = 10 MHz$		Room	-	-52	-	٩D
Channel-to-channel crosstalk d	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF$	f = 1 MHz f = 10 MHz	Room Room	-	-71 -55	-	dB
Off capacitance d	C _{S(off)}		1 - 10 1011 12		-	7	-	
COM off capacitance d	C _{COM(off)}	V+ = 5 V, f = 1 MHz		Room	-	27	_	рF
COM on capacitance d	C _{COM(off)}			Room	_	36	_	۲,
Power Supply	OCONI(ON)			1.00111	1	1 30	<u> </u>	
Power supply range	V+			Full	4.5	T -	5.5	V
Power supply current d	I+	V+ = 5.5 V V _{A/EN} - 0 V or 5.5 V se	e truth table	Full		+	1	μA
i ower supply current	i†	$V+=5.5~V,~V_{A/EN}=0~V~or~5.5~V,~see~truth~table$		ı uli			_ '	μΛ

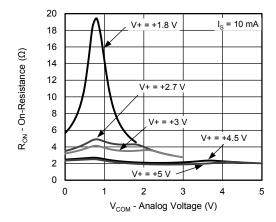
Notes

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- b. Typical values are for design aid only, not guaranteed nor subject to production testing
- c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- d. Guarantee by design, not subjected to production test
- e. V_A , EN = input voltage to perform proper function
- f. Difference of min. and max. values
- g. Guaranteed by 5 V testing

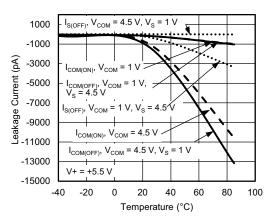
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



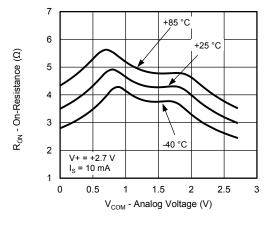
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



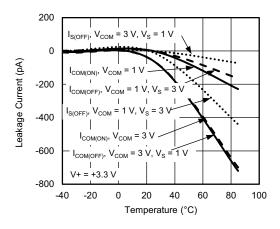
On-Resistance vs. Analog Voltage



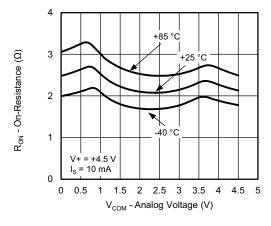
Leakage Current vs. Temperature



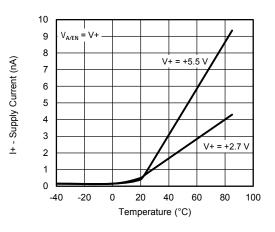
On-Resistance vs. Analog Voltage



Leakage Current vs. Temperature



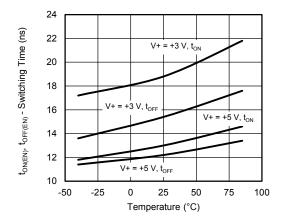
On-Resistance vs. Analog Voltage



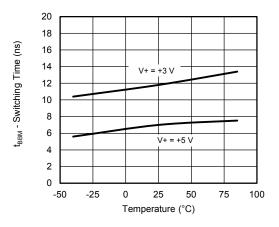
Supply Current vs. Temperature



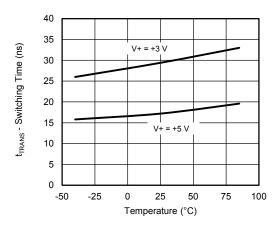
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



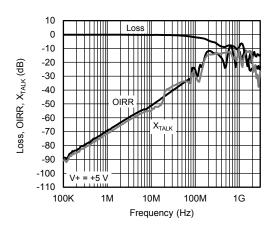
Switching Time vs. Temperature



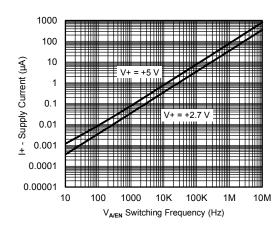
Switching Time vs. Temperature



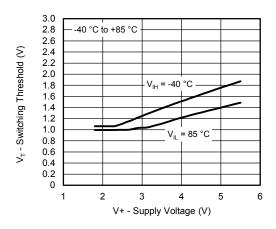
Switching Time vs. Temperature



Loss, OIRR, X_{TALK} vs. Frequency



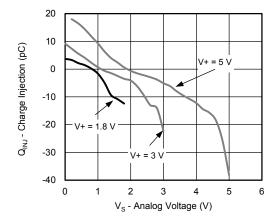
Positive Supply Current vs. Switching Frequency

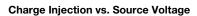


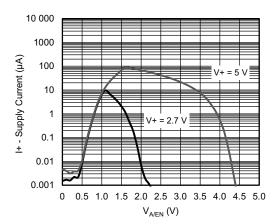
Switching Threshold vs. Supply Voltage



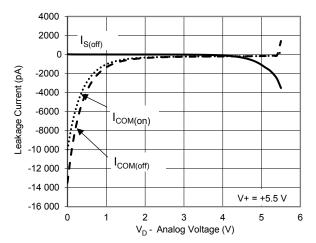
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







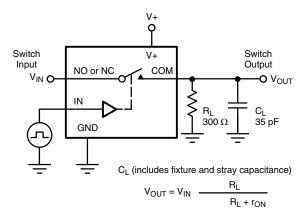
Positive Supply Current vs. Logic Voltage

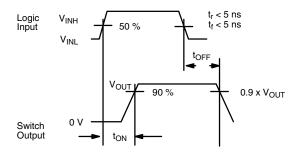


Leakage Current vs. Analog Voltage



TEST CIRCUITS





Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Fig. 1 - Switching Time

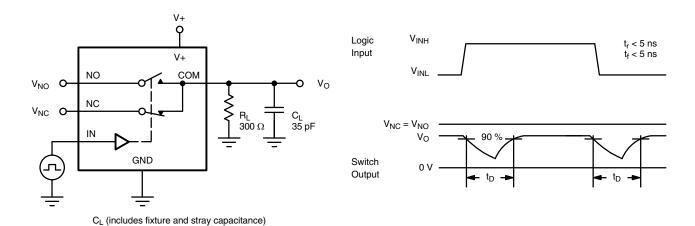


Fig. 2 - Break-Before-Make

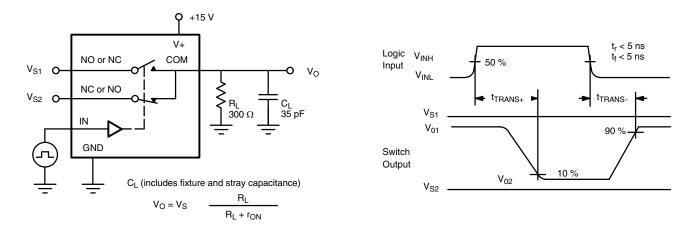
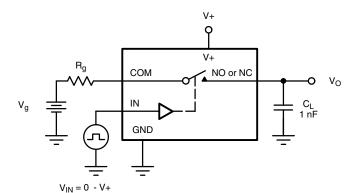
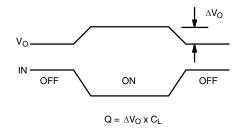


Fig. 3 - Transition Time



TEST CIRCUITS





IN dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection

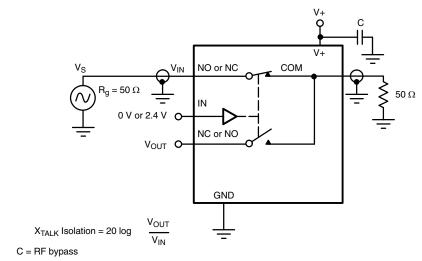


Fig. 5 - Crosstalk

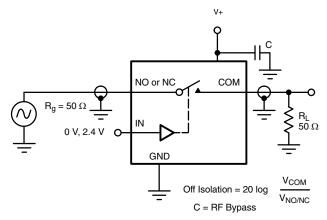


Fig. 6 - Off Isolation

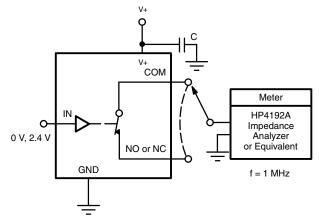


Fig. 7 - Source / Drain Capacitances

TEST CIRCUITS

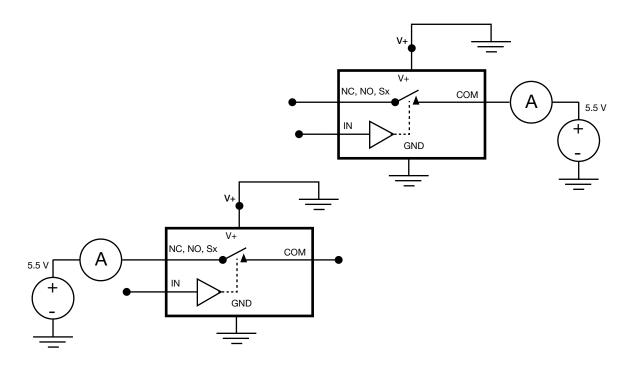


Fig. 8 - Source / Drain Power Down Leakage

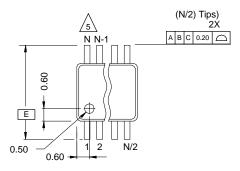
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73172.



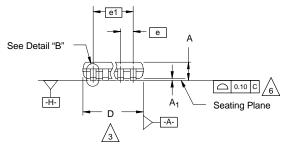


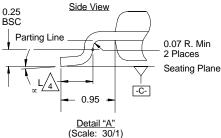
MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)



Top View





NOTES:

. Die thickness allowable is 0.203 ± 0.0127 .

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

<u>3.</u> D

Dimensions "D" and "E $_1$ " do not include mold flash or protrusions, and are measured at Datum plane $\boxed{-H_2}$, mold flash or protrusions shall not exceed 0.15 mm per side.



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

9. Controlling dimension: millimeters.

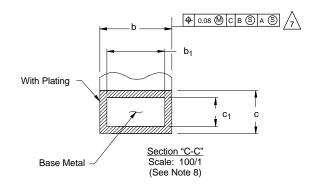
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

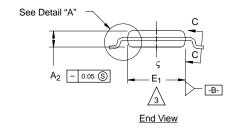


Datums -A- and -B- to be determined Datum plane -H-.

Exposed pad area in bottom side is the same as teh leadframe pad size.





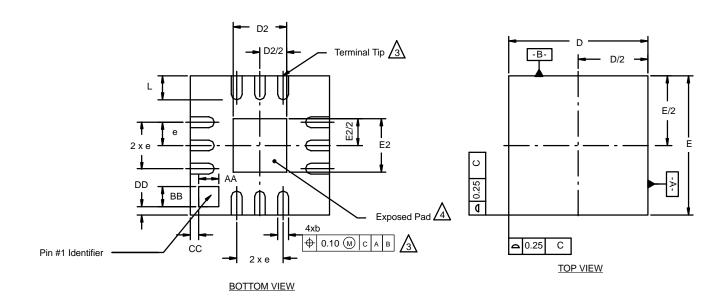


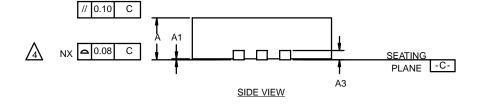
N = 10L

	M				
Dim	Min	Min Nom Max		Note	
Α	-	-	1.10		
A ₁	0.05	0.10	0.15		
A ₂	0.75	0.85	0.95		
b	0.17	-	0.27	8	
b ₁	0.17	0.20	0.23	8	
С	0.13	-	- 0.23		
c ₁	0.13	0.13 0.15 0.18			
D		3.00 BSC			
Е		4.90 BSC			
E ₁	2.90	3.00 3.10		3	
е		0.50 BSC			
e ₁		2.00 BSC			
L	0.40	0.55	0.70	4	
N		5			
οc	0°	4°	6°		



QFN-12 LEAD (3 X 3)





NOTES:

- 1. All dimensions are in millimeters.
- 2. N is the total number of terminals.

3.

Dimension b applies to metallized terminal and is measured between 0.25 and 0.30 mm from terminal tip. $\,$

4

Coplanarity applies to the exposed heat sink slug as well as the terminal.

The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.

	MILLIMETERS INCHES						
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.80	0.90	1.00	0.032	0.035	0.039	
b	0.18	0.23	0.30	0.007	0.009	0.012	
D		3.00 BSC			0.118 BSC		
D2	1.00	1.15	1.25	0.039	0.045	0.049	
Е	3.00 BSC			0.118 BSC			
E2	1.00	1.15	1.25	0.039 0.045 0.0			
е	0.50 BSC 0.02 BSC						
L	0.45	0.55	0.65	0.018	0.022	0.026	
AA		0.435			0.017		
BB	0.435 0.017						
CC	0.18 0.007						
DD	0.18 0.007						
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